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determining whether one or more empty spaces that are positioned outside the first areas require dummy fillings to facilitate an even polishing of a surface of the semiconductor die during CMP polishing;

forming a plurality of conductive layers within at least one of the empty spaces which are determined to require dummy fillings so as to form a test structure, wherein a top conductive layer of the plurality of conductive layers within the at least one of the empty spaces which are determined to require dummy fillings includes a dummy filling coupled to the test structure.

54. (Amended Once) A method of fabricating a test structure on a semiconductor die, comprising:

providing a semiconductor die having a plurality of first areas which are specified by a design as containing structures selected from a group consisting of a product structure and a test structure;

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determining whether one or more empty spaces that are positioned outside the first areas require dummy fillings to facilitate an even polishing of a surface of the semiconductor die during CMP polishing;

forming a plurality of dummy fillings within the empty spaces determined to require dummy fillings; and

forming a test structure from at least a portion of at least one of the dummy filling.

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58. (Amended Once) A method as recited in claim 56, further comprising performing voltage contrast inspection on the dummy fillings to detect a defect, wherein a defect is detected when the at least one dummy filling coupled to the test structure does not have a voltage potential that differs from a voltage potential of the other non-coupled dummy fillings.

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107. (New) A method as recited in claim 7, further comprising:

forming a plurality of conductive layers within at least one of the empty spaces which are determined to require dummy fillings so as to form a first test structure and a second test structure, wherein the first test structure is coupled with the substrate of the semiconductor die and the second test structure is not and wherein at least one of the dummy fillings is coupled to the first test structure and at least one of the dummy filling is coupled to the second test structure;

performing voltage contrast inspection on the first and second test structures to detect a defect within the first and second test structure, wherein a defect is detected when the first test structure differs from a voltage potential of the second test structure.